# Contents

List of Contributors Foreword Preface		vii ix xi
1	The Measurement of Residual Stresses by X-Ray Diffraction Techniques	
	M. R. James and J. B. Cohen	
	I. Introduction	2
	II. Types of Residual Stresses	2
	III. Principles of X-Ray Stress Measurement	4
	IV. Control of Accuracy and Precision	25
	V. Fundamental Problems	35
	VI. Applications	45
	References	55
2	The Investigation of Composition	
	Variations by Diffraction	
	C. R. Houska	
	I. Introduction	63
	II. Diffraction Equations	68
	III. Penetration Distance	75
	IV. Effective Volume Calculations	75
	V. Two Methods of Analyzing for Composition Profile	79
	VI. Choice of Binary System for Composition	
	Broadening Studies	86
	VII. Analysis of Rocking Curve Data	87
	VIII. Influence of Temperature Diffuse Scattering	88
	IX. Determinations of Composition Profiles	89
	X. Summary	101
	References	104

#### 3 The Use of Mössbauer Spectroscopy in Materials Science

## Geoffrey Longworth

I.	Introduction	108
II.	General Principles of Mössbauer Spectroscopy	108
III.	Instrumentation	114
IV.	Measurements on Substitutional Alloys	121
V.	Interstitial Alloys	130
VI.	Magnetic Studies	138
VII.	Phase Analysis	142
VIII.	Summary	145
	References	147

### 4 Photoluminescence Techniques for Studies of Composition and Defects in Semiconductors

#### B. Monemar

I.	Introduction	151
II.	Equipment for Photoluminescence Experiments	156
III.	Profiling of Bulk Properties of Semiconductors	
	with Photoluminescence	158
IV.	Some Applications of Photoluminescence	
	in the Exploration of Properties	
	of Point Defects in Semiconductors	174
V.	Studies of Dislocation-Related Defects in Semiconductors	
	with Photoluminescence Techniques	197
	References	207

# 5 Materials Production by High Rate Sputter Deposition

# S. D. Dahlgren

I.	Introduction	213
II.	High Rate Sputtering Systems	214
III.	Sputter-Deposition Techniques	216
IV.	Sputter-Deposited Materials	244
	References	250

Index	253
Contents of Previous Volumes	257

vi